TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74HCT174AP,TC74HCT174AF,TC74HCT174AFN

Hex D-Type Flip Flop with Clear

The TC74HCT174A is a high speed CMOS D-TYPE FLIP FLOP fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

Information signals applied to the D inputs are transferred to the Q outputs on the positive going edge of the clock pulse.

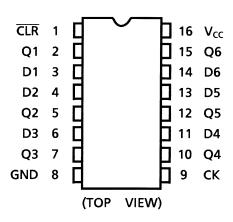
When the  $\overline{\text{CLR}}$  input is held low, the Q outputs are in the low logic level independent of the other inputs.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

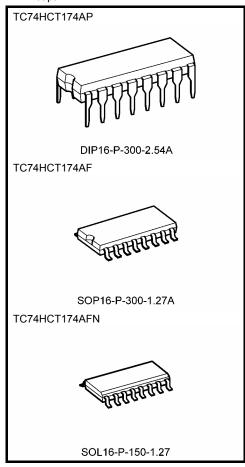
#### **Features**

- High speed:  $f_{max} = 56 \text{ MHz}$  (typ.) at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max)}$  at  $T_a = 25^{\circ}C$
- Compatible with TTL outputs:  $V_{IH}$  = 2.0 V (min)  $V_{IL}$  = 0.8 V (max)
- Wide interfacing ability: LSTTL, NMOS, CMOS
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: | I<sub>OH</sub> | = I<sub>OL</sub> = 4 mA (min)
- Balanced propagation delays:  $t_pLH \simeq t_pHL$
- Pin and function compatible with 74LS174

#### **Pin Assignment**



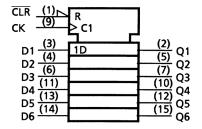
Note: xxxFN (JEDEC SOP) is not available in Japan.



Weight

DIP16-P-300-2.54A : 1.00 g (typ.) SOP16-P-300-1.27A : 0.18 g (typ.) SOL16-P-150-1.27 : 0.13 g (typ.)

# **IEC Logic Symbol**

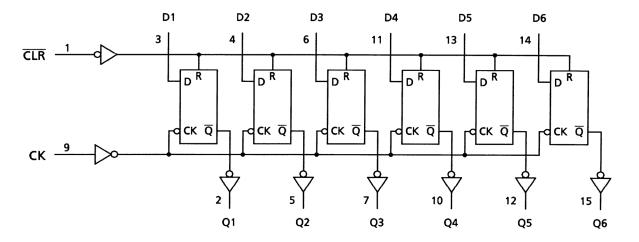


### **Truth Table**

	Inputs		Output	Function
CLR	D	CK	Q	Tunction
L	Х	Х	L	Clear
Н	L		L	_
Н	Н		Н	_
Н	Х		Qn	No Change

X: Don't care

### **System Diagram**





### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	−0.5 to 7	V
DC input voltage	V <sub>IN</sub>	−0.5 to V <sub>CC</sub> + 0.5	٧
DC output voltage	V <sub>OUT</sub>	$-0.5$ to $V_{CC} + 0.5$	V
Input diode current	Ι <sub>ΙΚ</sub>	±20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	$P_{D}$	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T <sub>stg</sub>	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to  $65^{\circ}C$ . From Ta = 65 to  $85^{\circ}C$  a derating factor of -10 mW/°C shall be applied until 300 mW.

### **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	4.5 to 5.5	V
Input voltage	$V_{IN}$	0 to V <sub>CC</sub>	V
Output voltage	V <sub>OUT</sub>	0 to V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
Input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0 to 500	ns

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40 to 85°C		- Unit
				V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
High-level input voltage	V <sub>IH</sub>	_		4.5 to 5.5	2.0	_	_	2.0	_	V
Low-level input voltage	V <sub>IL</sub>	_		4.5 to 5.5	_	_	0.8	_	0.8	V
High-level output	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -20 \mu A$	4.5	4.4	4.5	-	4.4	_	٧
voltage			I <sub>OH</sub> = -4 mA	4.5	4.18	4.31		4.13	_	
Low-level output	.,	V <sub>IN</sub>	$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	-	0.1	.,
voltage	V <sub>OL</sub>	= V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 4 mA	4.5	_	0.17	0.26	_	0.33	V
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	±0.1	_	±1.0	μА
Quiescent supply current	Icc	$V_{IN} = V_C$	V <sub>IN</sub> = V <sub>CC</sub> or GND		_		4.0		40.0	μΑ
	Ic		Per input: V <sub>IN</sub> = 0.5 V or 2.4 V Other input: V <sub>CC</sub> or GND		_	_	2.0		2.9	mA



# Timing Requirements (input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition	Test Condition			Ta = -40 to 85°C	Unit	
			V <sub>CC</sub> (V)	Тур.	Limit	Limit		
Minimum pulse width	t <sub>W (L)</sub>		4.5	_	15	19	no	
(CK)	t <sub>W (H)</sub>	_	5.5	_	14	18	ns	
Minimum pulse width	<b>4</b>		4.5	_	15	19	20	
(CLR)	t <sub>W (L)</sub>	_	5.5	_	14	18	ns	
Minimum act un tima	t <sub>s</sub>	_	4.5	_	20	25	20	
Minimum set-up time			5.5	_	18	23	ns	
Minimum hold time	4		4.5	_	5	5	ns	
Willimitati noid time	t <sub>h</sub>		5.5	_	5	5	115	
Minimum removal time	4		4.5		10	10	20	
(CLR)	t <sub>rem</sub>	_	5.5	_	10	10	ns	
Cleak fraguency	f		4.5	_	30	24	MIL	
Clock frequency		_	5.5	_	33	26	MHz	

# AC Characteristics (C $_L$ = 15 pF, $V_{CC}$ = 5 V, Ta = 25 $^{\circ}\text{C},$ input: $t_r$ = $t_f$ = 6 ns)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Output transition time	t <sub>TLH</sub> t <sub>THL</sub>	_	_	12	15	ns
Propagation delay time (CK-Q)	t <sub>pLH</sub>	_	_	29	36	ns
Propagation delay time ( CLR -Q)	t <sub>pHL</sub>	_	_	29	36	ns
Maximum clock frequency	f <sub>max</sub>	_	32	61		MHz



### AC Characteristics ( $C_L = 50 \text{ pF}$ , input: $t_r = t_f = 6 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
	,		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
Output transition time	t <sub>TLH</sub>		4.5	_	8	15	_	19	20
Output transition time	t <sub>THL</sub>	_	5.5	_	7	14	_	18	ns
Propagation delay time	t <sub>pLH</sub>	_	4.5	_	20	34	_	43	ns
(CK-Q)	t <sub>pHL</sub>		5.5		17	31	_	39	
Propagation delay time	t <sub>pHL</sub>	_	4.5	_	20	34	_	43	ns
( CLR -Q)	∙рп∟		5.5		17	31	_	39	110
Maximum clock	£		4.5	30	54	_	24	_	MHz
frequency	f <sub>max</sub>	_	5.5	33	57	_	26	_	IVITZ
Input capacitance	C <sub>IN</sub>	_		_	5	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub> (Note)	_		_	30	_	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

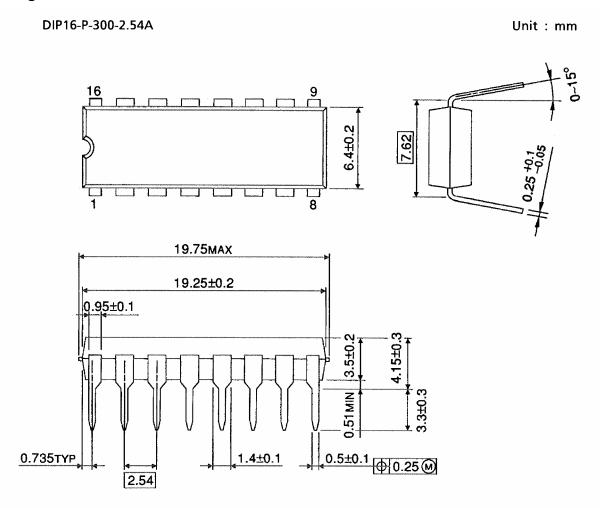
Average operating current can be obtained by the equation:

$$I_{CC} \; (opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \; (per \; F/F)$$

And the total C<sub>PD</sub> when n pcs. of flip flop operate can be gained by the following equation:

$$C_{PD}$$
 (total) = 18 + 12 · n

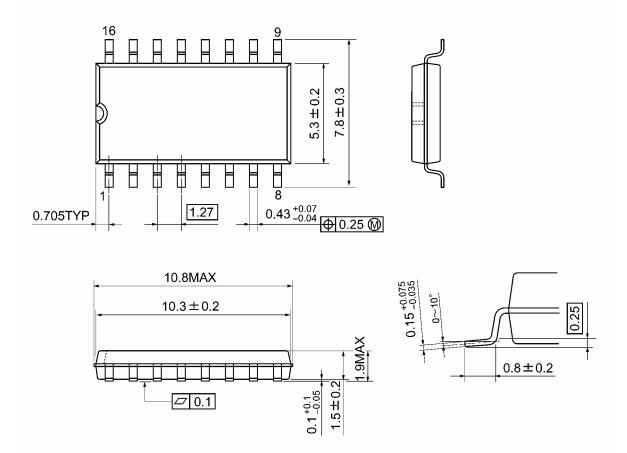
# **Package Dimensions**



Weight: 1.00 g (typ.)

# **Package Dimensions**

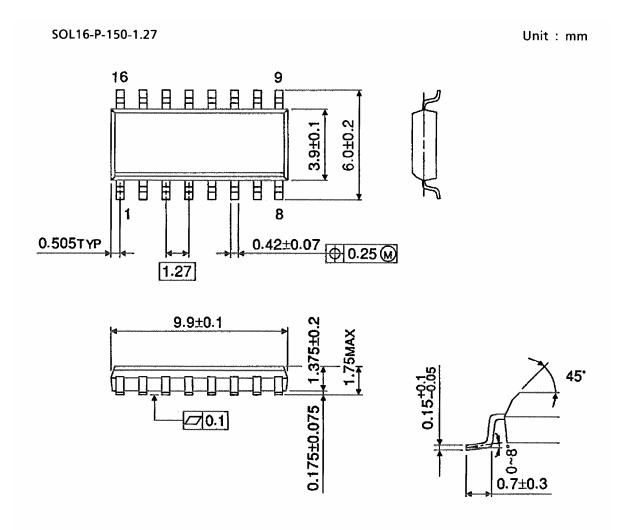
SOP16-P-300-1.27A Unit: mm



Weight: 0.18 g (typ.)



# **Package Dimensions (Note)**



8

Note: This package is not available in Japan.

Weight: 0.13 g (typ.)

#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN GENERAL

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
  compatibility. Please use these products in this document in compliance with all applicable laws and regulations
  that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
  occurring as a result of noncompliance with applicable laws and regulations.